

L Number	Hits	Search Text	DB	Time stamp
1	11209	substrate near3 bias	USPAT; US-PGPUB; EPO; JPO	2004/05/24 15:54
2	974	((substrate near3 bias) same voltage same insulat\$4	USPAT; US-PGPUB; EPO; JPO	2004/05/24 15:54
3	2	((substrate near3 bias) same voltage same insulat\$4) same stem	USPAT; US-PGPUB; EPO; JPO	2004/05/24 15:56
4	52	((substrate near3 bias) same voltage same insulat\$4) same base	USPAT; US-PGPUB; EPO; JPO	2004/05/24 15:56
5	1	((((substrate near3 bias) same voltage same insulat\$4) same base) same (optical light)	USPAT; US-PGPUB; EPO; JPO	2004/05/24 15:57
6	52	((((substrate near3 bias) same voltage same insulat\$4) same base)	USPAT; US-PGPUB; EPO; JPO	2004/05/24 15:57

L Number	Hits	Search Text	DB	Time stamp
1	9	(stem base) same optical same (insulat\$4 dioxide SiO2) same (revers\$4 near2 voltage)	USPAT; US-PGPUB; EPO; JPO	2004/05/24 14:31
2	14	(stem base) same optical same (insulat\$4 dioxide SiO2) same (revers\$4 near2 (voltage bias))	USPAT; US-PGPUB; EPO; JPO	2004/05/24 14:44
3	271	(stem base) same optical same (insulat\$4 dioxide SiO2) same (voltage bias)	USPAT; US-PGPUB; EPO; JPO	2004/05/24 14:45
4	19	((stem base) same optical same (insulat\$4 dioxide SiO2) same (voltage bias)) same laser	USPAT; US-PGPUB; EPO; JPO	2004/05/24 14:45

L Number	Hits	Search Text	DB	Time stamp
1	14	substrate same base same stem same (insulat\$4 near2 (member layer surface))	USPAT; US-PGPUB; EPO; JPO	2004/05/24 09:55
2	1713	substrate and base and stem and ((insulat\$4 dielectric) near2 (member layer surface))	USPAT; US-PGPUB; EPO; JPO	2004/05/24 09:56
3	4405	substrate same stem	USPAT; US-PGPUB; EPO; JPO	2004/05/24 09:57
4	432	(substrate and base and stem and ((insulat\$4 dielectric) near2 (member layer surface))) and (substrate same stem)	USPAT; US-PGPUB; EPO; JPO	2004/05/24 09:58
5	42	(substrate same stem) same voltage same (insulat\$4 dielectric)	USPAT; US-PGPUB; EPO; JPO	2004/05/24 10:09
6	163	((substrate and base and stem and ((insulat\$4 dielectric) near2 (member layer surface))) and (substrate same stem)) and laser	USPAT; US-PGPUB; EPO; JPO	2004/05/24 10:09
7	95	((substrate and base and stem and ((insulat\$4 dielectric) near2 (member layer surface))) and (substrate same stem)) and laser) and PIN	USPAT; US-PGPUB; EPO; JPO	2004/05/24 10:10
8	0	((substrate and base and stem and ((insulat\$4 dielectric) near2 (member layer surface))) and (substrate same stem)) and laser) and (PIN adj diode)	USPAT; US-PGPUB; EPO; JPO	2004/05/24 10:10
9	1	((substrate and base and stem and ((insulat\$4 dielectric) near2 (member layer surface))) and (substrate same stem)) and laser) and (PIN near2 (photo adj diode))	USPAT; US-PGPUB; EPO; JPO	2004/05/24 10:11
10	20	((substrate and base and stem and ((insulat\$4 dielectric) near2 (member layer surface))) and (substrate same stem)) and laser) and (photodiode (photo adj diode))	USPAT; US-PGPUB; EPO; JPO	2004/05/24 10:11